

ABSTRACT

5 A method of forming a Bi-layered superlattice material on a substrate using chemical vapor deposition of a precursor solution of trimethylbismuth and a metal compound dissolved in an organic solvent. The precursor solution is heated and vaporized prior to deposition of the precursor solution on an integrated circuit substrate by chemical vapor deposition. No heating steps including a temperature of 650°C or higher are used.

13249.348